L Number	Hits	Search Text	DB	Time stamp
54	71	(134/902.ccls. and ((spin adj dry$3) or spin-dry$3 or spindry$3)) and (inert or nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 09:57
57	39	(134/21,30,33,37.ccls. and ((spin adj dry$3) or spin-dry$3 or spindry$3)) and (inert or nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 10:56
-	111	34/418.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:09
-	8	34/418.ccls. and (semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:11
-	459	34/443,487,510,516.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:11
-	39	34/443,487,510,516.ccls. and (semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:49
-	2588	134/21,30,33,37.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:19
-	208	134/21,30,33,37.ccls. and 134/902.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:19
-	11	(134/21,30,33,37.ccls. and 134/902.ccls.) and (spin?dry$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:20
-	111	((134/21,30,33,37.ccls. and 134/902.ccls.) and dry$3) and ((inert adj gas) or nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:32
-	60	(((134/21,30,33,37.ccls. and 134/902.ccls.) and dry$3) and ((inert adj gas) or nitrogen)) and (chuck or rotary or rotate or rotating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:42
-	312	134/21.ccls. and (chuck or rotary or rotate or rotating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:31

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-	335	438/906.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:40
-	0	438/906.ccls. and 134/153.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:45
-	29	438/906.ccls. and 134/902.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 14:59
-	61	438/906.ccls. and (chuck or rotary or rotate or rotating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:43
-	203	134/153.ccls. and dry$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 15:21
-	8	(134/153.ccls. and dry$3) and 34/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:47
-	30	134/153.ccls. and 34/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:47
-	1748	134/902.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:50
-	72	134/902.ccls. and 34/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 12:50
-	163	(134/21,30,33,37.ccls. and 134/902.ccls.) and dry$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 14:47
-	133	134/102.3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 14:47
-	42	134/102.3.ccls. and (semiconductor or wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 14:57
-	1	438/906.ccls. and 34/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 14:59

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-	121	(134/21.ccls. and (chuck or rotary or rotate or rotating)) and dry$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 15:01
-	9	134/153.ccls. and (spin?dry$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 15:31
-	63	134/$.ccls. and showerhead	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 15:54
-	1	(134/$.ccls. and showerhead) and (spin?dry$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 15:45
-	39	(134/$.ccls. and showerhead) and (dry$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 15:34
-	1	(134/$.ccls. and showerhead) and (spin-dry$3 or spindry$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 15:45
-	1	(134/$.ccls. and showerhead) and (spin-dry$3 or (spin adj dry$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 15:45
-	46	(134/$.ccls. and showerhead) and (inert or nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 15:46
-	10	34/$.ccls. and showerhead	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 15:56
-	134	34/$.ccls. and ((spin adj dry$3) or spin-dry$3 or spindry$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 16:17
-	49	(34/$.ccls. and ((spin adj dry$3) or spin-dry$3 or spindry$3)) and (inert or nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 09:37
-	81	(34/$.ccls. and ((spin adj dry$3) or spin-dry$3 or spindry$3)) and (semiconductor or wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 16:14
-	75	134/21,30,33,37.ccls. and ((spin adj dry$3) or spin-dry$3 or spindry$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 09:21

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